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Vishay Siliconix

AUTOMOTIVE

RoHS

COMPLIANT

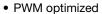
FREE

# Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V <sub>DS</sub> (V)	60
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.023
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.028
I <sub>D</sub> (A)	18
Configuration	Single

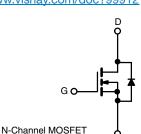
# FEATURES

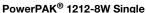
- TrenchFET® power MOSFET
- Low thermal resistance PowerPAK® 1212-8 package with 1.07 mm profile

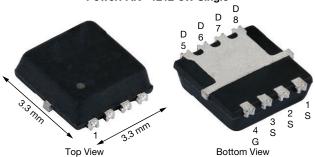


- 100 % R<sub>a</sub> and UIS tested
- AEC-Q101 qualified
- Wettable flank terminals

 Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912">www.vishav.com/doc?99912</a>







Marking Code: Q020

ORDERING INFORMATION	
Package	PowerPAK 1212-8W
Lead (Pb)-free and Halogen-free	SQ7414AENW-T1-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25$	°C, unless otherw	ise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	60	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	V
Continuous Duain Current 3	T <sub>C</sub> = 25 °C	I <sub>D</sub>	18	
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 125 °C		18	
Continuous Source Current (Diode Conduction) a		I <sub>S</sub>	18	Α
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	72	
Single Pulse Avalanche Current		I <sub>AS</sub>	20	
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	16	mJ
Mayimum Daylar Dissination h	T <sub>C</sub> = 25 °C	P <sub>D</sub>	62	W
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C		20	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	00
Soldering Recommendations (Peak Temperature) d			260	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	81	°C/W
Junction-to-Case (Drain)		R <sub>thJC</sub>	2.4	C/VV

### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR4 material).
- d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						L	l
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		60	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	· V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2	2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	=.	-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	20	-	-	Α
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 8.7 A	-	0.016	0.023	Ω
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 8.7 A, T <sub>J</sub> = 125 °C	-	-	0.039	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 8.7 A, T <sub>J</sub> = 175 °C	-	-	0.050	
		$V_{GS} = 4.5 \text{ V}$	I <sub>D</sub> = 8.7 A	-	0.019	0.028	
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> :	= 15 V, I <sub>D</sub> = 8.7 A	i	50	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			'n	1275	1590	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$	1	112	140	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	42	52	
Total Gate Charge <sup>c</sup>	Qg			'n	19	25	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = 10 \text{ V}$	$V_{DS} = 30 \text{ V}, I_{D} = 8.7 \text{ A}$	-	2.6	-	nC
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	3.6	-	
Gate Resistance	$R_g$	f = 1 MHz		0.6	1.12	1.6	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			=.	8	10	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 30 \text{ V}, R_{L} = 30 \Omega$		=	13	16	]
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 1 \text{ A}, Y$	$V_{\rm GEN} = 10 \text{ V}, R_{\rm g} = 1 \Omega$	-	22	26	ns
Fall Time <sup>c</sup>	t <sub>f</sub>			-	15	18	
Source-Drain Diode Ratings and Chara	acteristics b						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			=.	-	72	Α
Forward Voltage	$V_{SD}$	$I_F = 8.7 \text{ A}, V_{GS} = 0 \text{ V}$		-	0.8	1.2	V

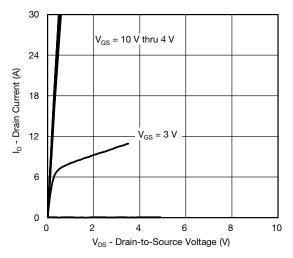
### Notes

- a. Pulse test; pulse width  $\leq 300 \,\mu\text{s}$ , duty cycle  $\leq 2 \,\%$ .
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

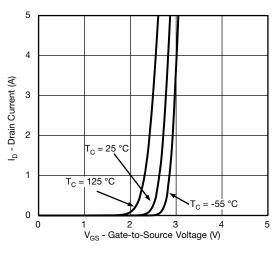
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



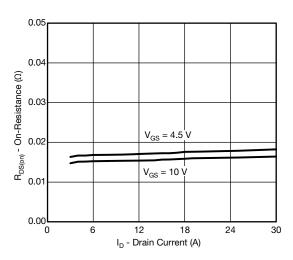
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



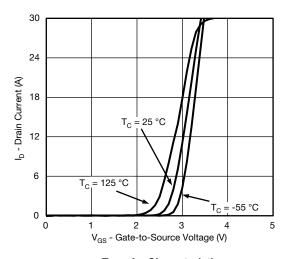
#### **Output Characteristics**



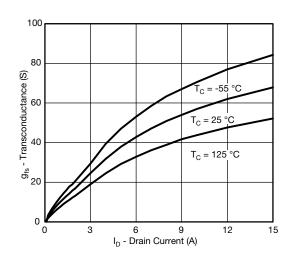
### **Transfer Characteristics**



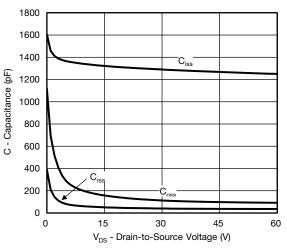
On-Resistance vs. Drain Current



#### **Transfer Characteristics**



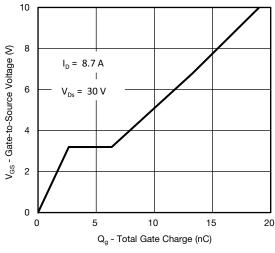
#### Transconductance



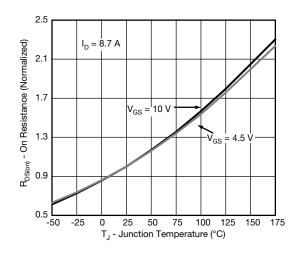
Capacitance



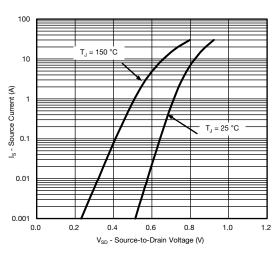
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



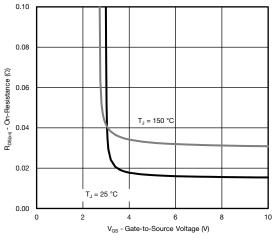
**Gate Charge** 



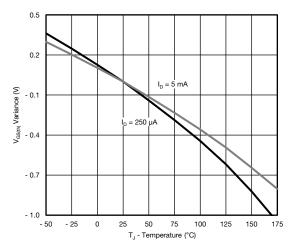
**On-Resistance vs. Junction Temperature** 



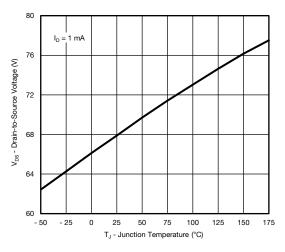
**Source Drain Diode Forward Voltage** 



On-Resistance vs. Gate-to-Source Voltage



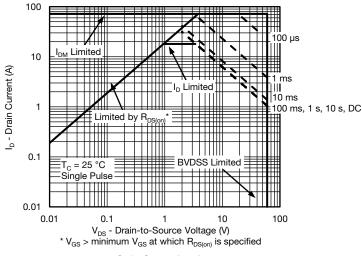
**Threshold Voltage** 



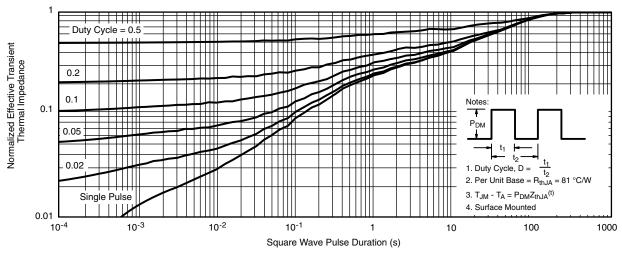
Drain Source Breakdown vs. Junction Temperature



### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



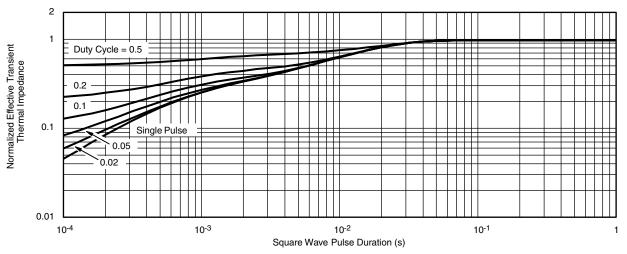
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg262980">www.vishay.com/ppg262980</a>.



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## PowerPAK® 1212-8 and PowerPAK 1212-8W

Ordering codes for the SQ rugged series power MOSFETs in the PowerPAK 1212-8 and PowerPAK 1212-8W packages:

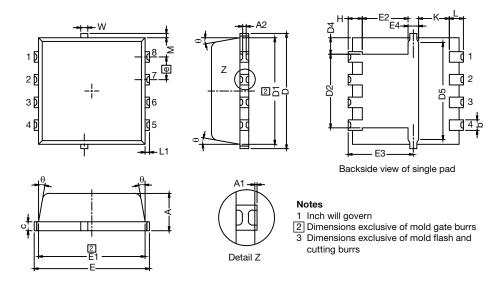
DATASHEET PART NUMBER	OLD ORDERING CODE <sup>a</sup>	NEW ORDERING CODE
SQ7414AEN	SQ7414AEN-T1-GE3	SQ7414AEN-T1_GE3
SQ7414AENW	-	SQ7414AENW-T1_GE3
SQ7415AEN	SQ7415AEN-T1-GE3	SQ7415AEN-T1_GE3
SQ7415AENW	-	SQ7415AENW-T1_GE3
SQS401EN	SQS401EN-T1-GE3	SQS401EN-T1_GE3
SQS401ENW	-	SQS401ENW-T1_GE3
SQS405EN	SQS405EN-T1-GE3	SQS405EN-T1_GE3
SQS405ENW	-	SQS405ENW-T1_GE3
SQS420EN	SQS420EN-T1-GE3	SQS420EN-T1_GE3
SQS423EN	SQS423EN-T1-GE3	SQS423EN-T1_GE3
SQS460EN	SQS460EN-T1-GE3	SQS460EN-T1_GE3
SQS462EN	SQS462EN-T1-GE3	SQS462EN-T1_GE3
SQS482EN	SQS482EN-T1-GE3	SQS482EN-T1_GE3
SQS484EN	SQS484EN-T1-GE3	SQS484EN-T1_GE3
SQS490EN	SQS490EN-T1-GE3	SQS490EN-T1_GE3
SQS840EN	SQS840EN-T1-GE3	SQS840EN-T1_GE3
SQS850EN	SQS850EN-T1-GE3	SQS850EN-T1_GE3

#### Note

a. Old ordering code is obsolete and no longer valid for new orders



## PowerPAK® 1212-8W Case Outline



DIM.	MILLIMETERS			INCHES			
DIIVI.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.97	1.04	1.12	0.038	0.041	0.044	
A1	0	-	0.05	0	-	0.002	
A2	0	-	0.13	0	-	0.005	
b	0.23	0.30	0.41	0.009	0.012	0.016	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.95	3.05	3.15	0.116	0.120	0.124	
D2	1.98	2.11	2.24	0.078	0.083	0.088	
D4		0.47 typ.		0.0185 typ.			
D5		2.3 typ.			0.090 typ.		
Е	3.20	3.30	3.40	0.126	0.130	0.134	
E1	2.95	3.05	3.15	0.116	0.120	0.124	
E2	1.47	1.60	1.73	0.058	0.063	0.068	
E3	1.75	1.85	1.98	0.069	0.073	0.078	
E4		0.34 typ.			0.013 typ.		
е	0.65 BSC.				0.026 BSC		
K	0.86 typ.				0.034 typ.		
Н	0.30	0.41	0.51	0.012	0.016	0.020	
L	0.30	0.43	0.56	0.012	0.017	0.022	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
М		0.125 typ.			0.005 typ.		

DWG: 6032



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Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Revision: 02-Oct-12 Document Number: 91000